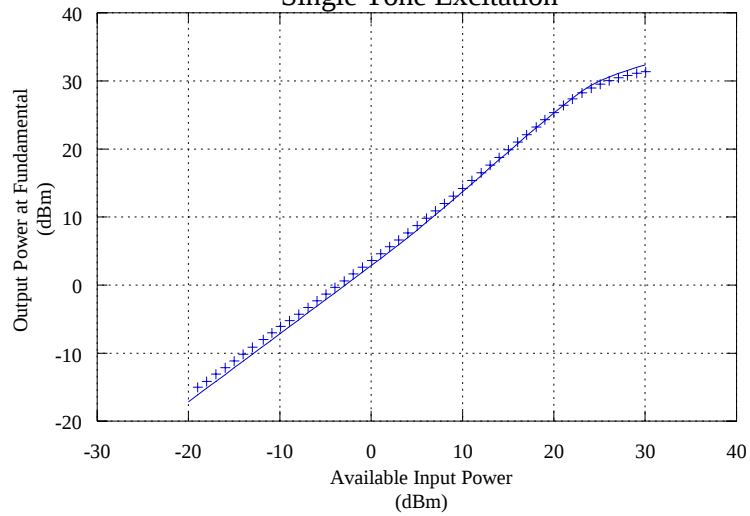
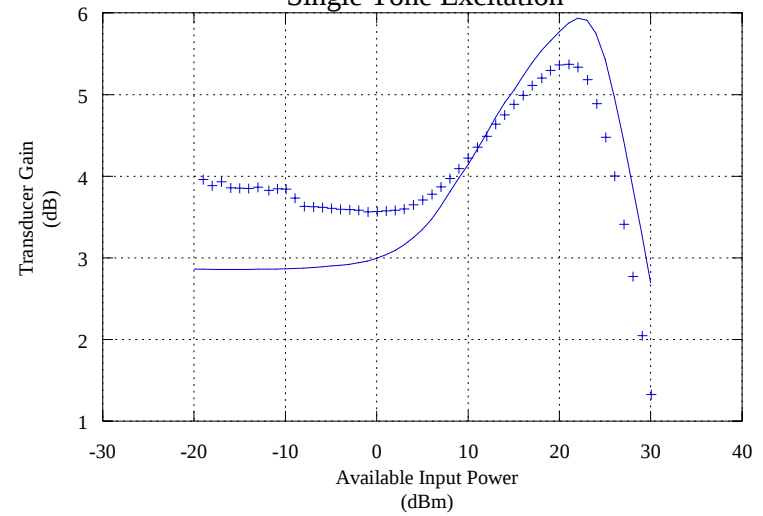


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 50 ohm Termination
 Solid: Simulated & Points: Measured

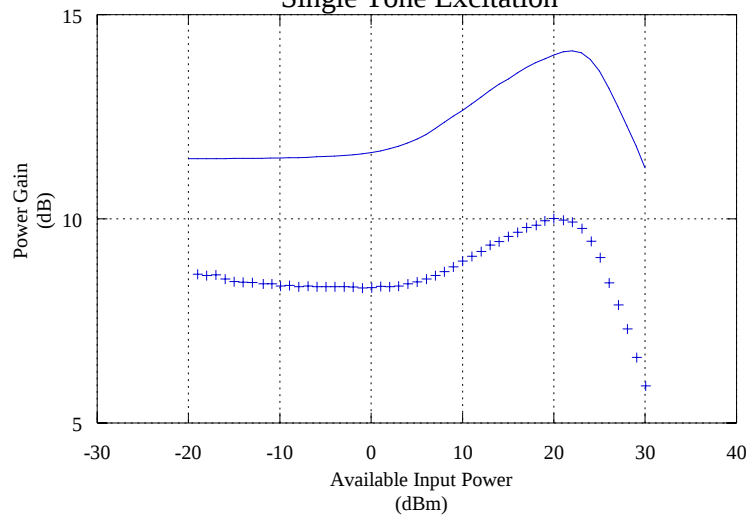
Output Power at Fundamental vs. Available Input Power
 Single Tone Excitation



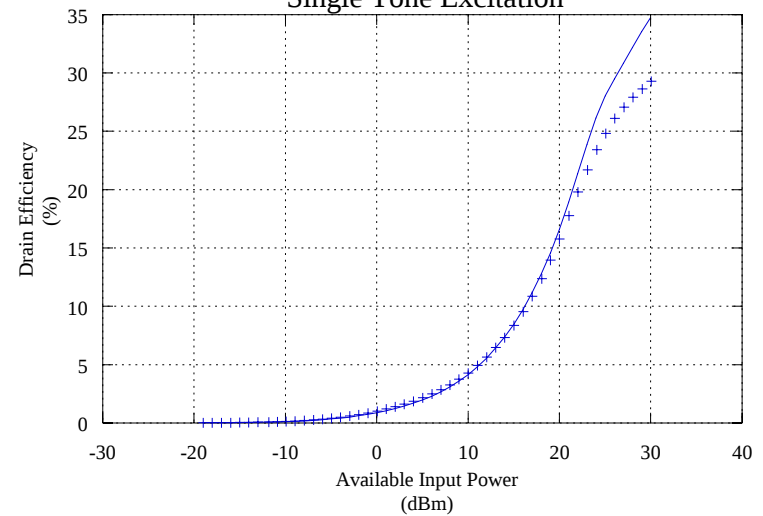
Transducer Gain vs. Available Input Power
 Single Tone Excitation



Power Gain vs. Available Input Power
 Single Tone Excitation

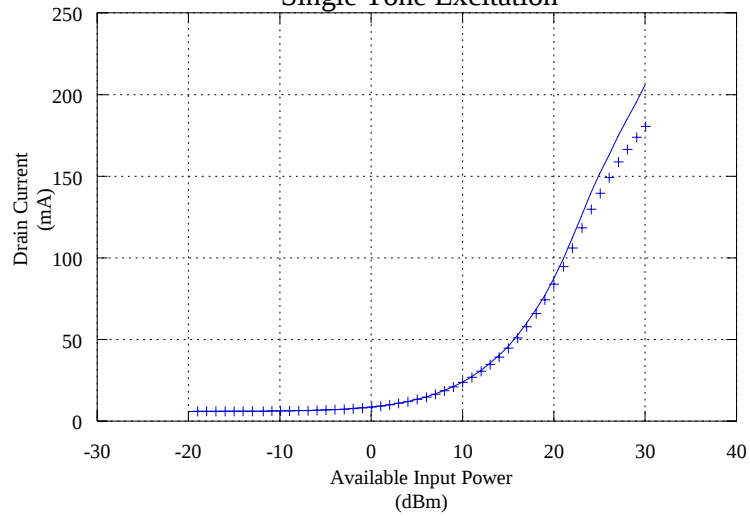


Drain Efficiency vs. Available Input Power
 Single Tone Excitation

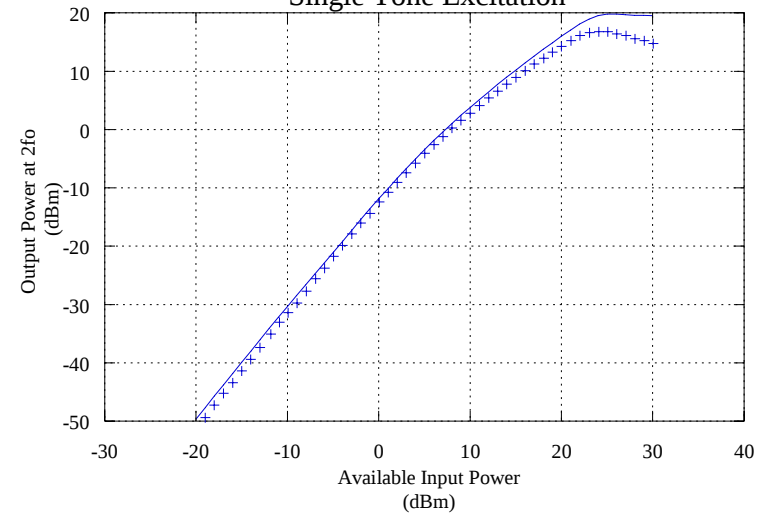


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 50 ohm Termination
 Solid: Simulated & Points: Measured

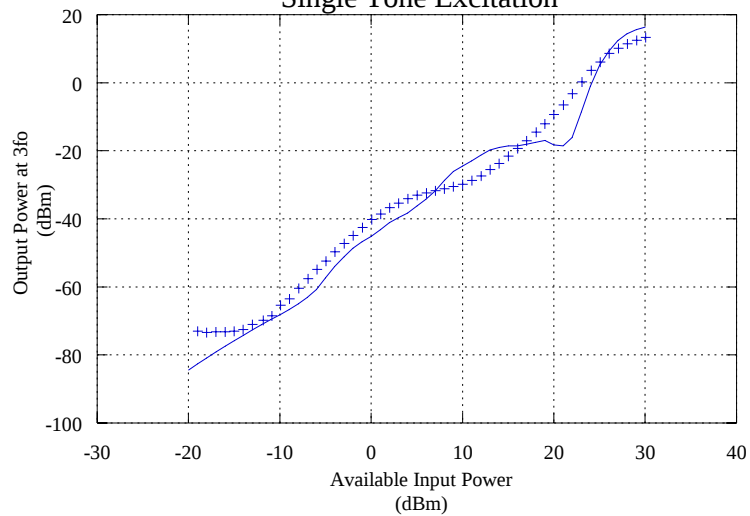
Drain Current vs. Available Input Power
 Single Tone Excitation



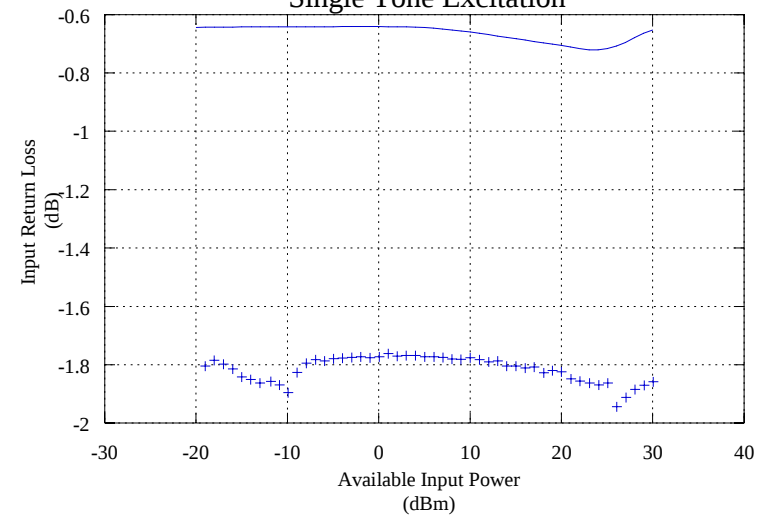
Output Power at 2fo vs. Available Input Power
 Single Tone Excitation



Output Power at 3fo vs. Available Input Power
 Single Tone Excitation

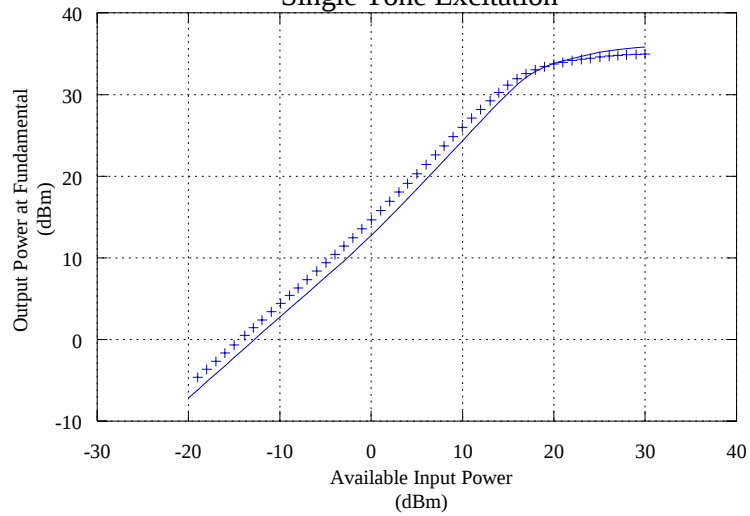


Input Return Loss vs. Available Input Power
 Single Tone Excitation

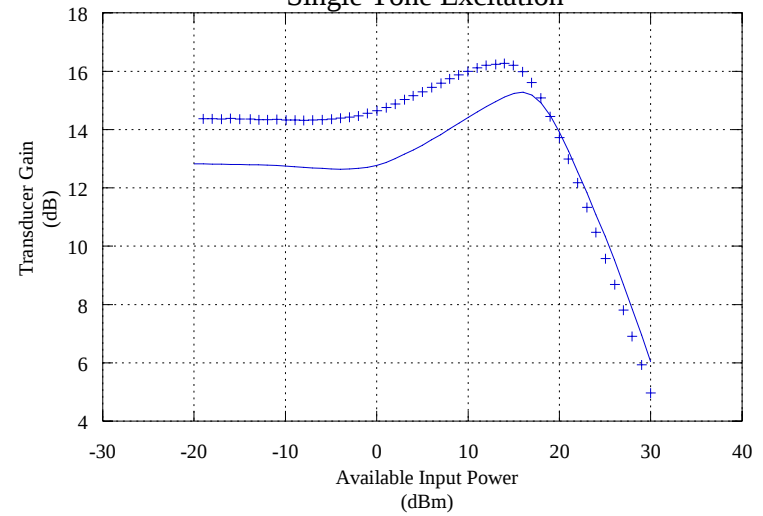


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 Tuned for Power
 Solid: Simulated & Points: Measured

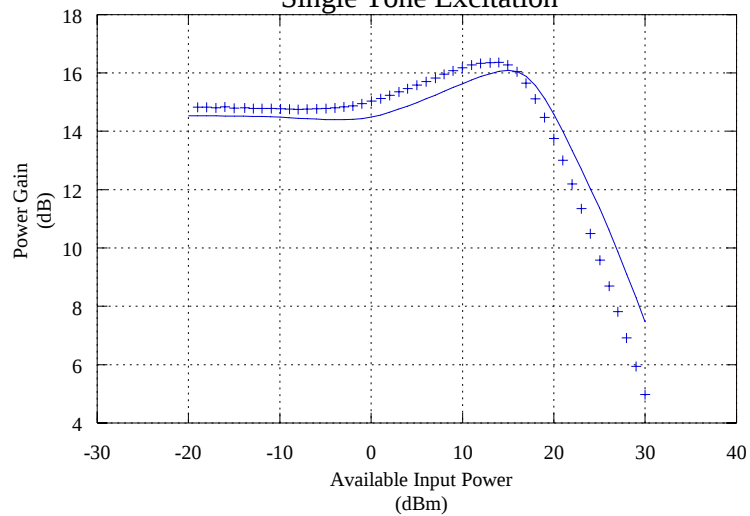
Output Power at Fundamental vs. Available Input Power
 Single Tone Excitation



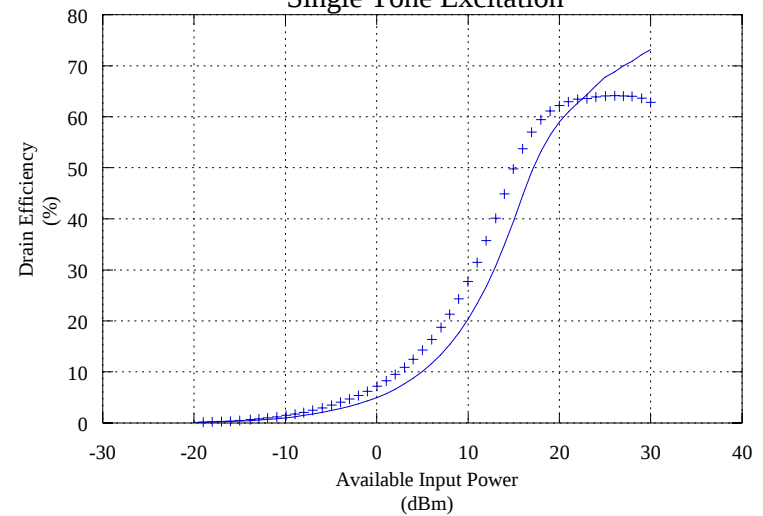
Transducer Gain vs. Available Input Power
 Single Tone Excitation



Power Gain vs. Available Input Power
 Single Tone Excitation

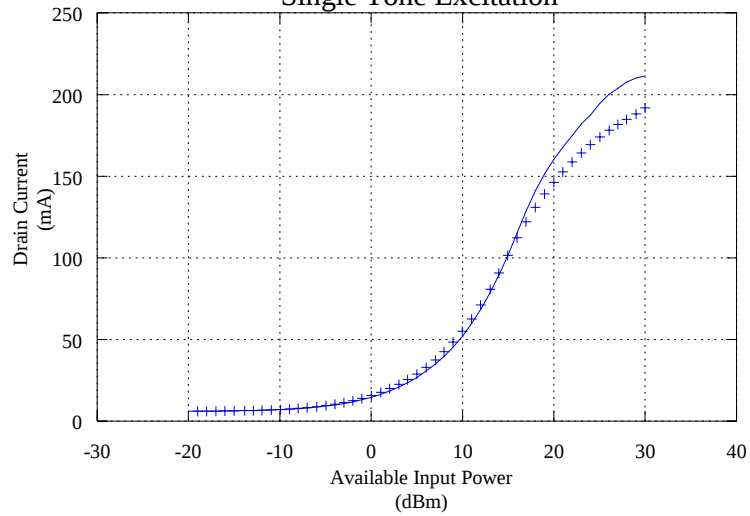


Drain Efficiency vs. Available Input Power
 Single Tone Excitation

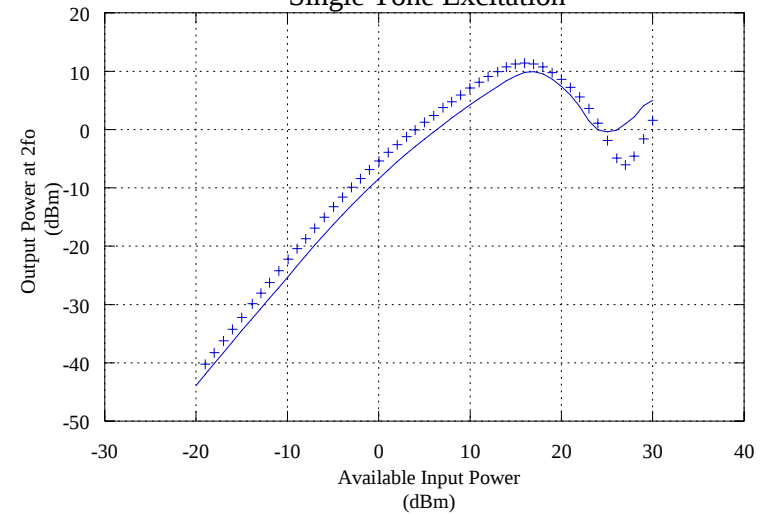


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 Tuned for Power
 Solid: Simulated & Points: Measured

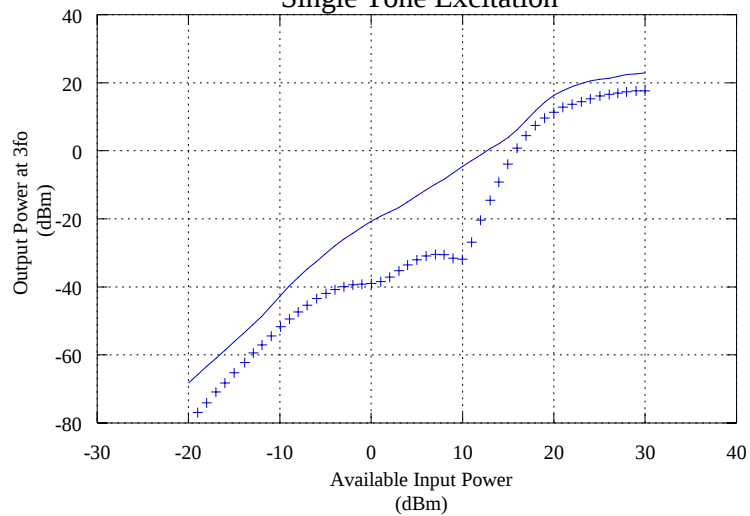
Drain Current vs. Available Input Power
 Single Tone Excitation



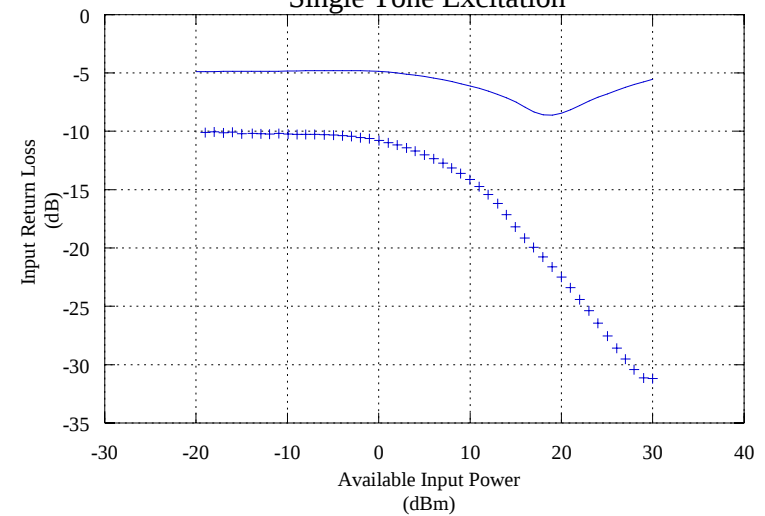
Output Power at 2fo vs. Available Input Power
 Single Tone Excitation



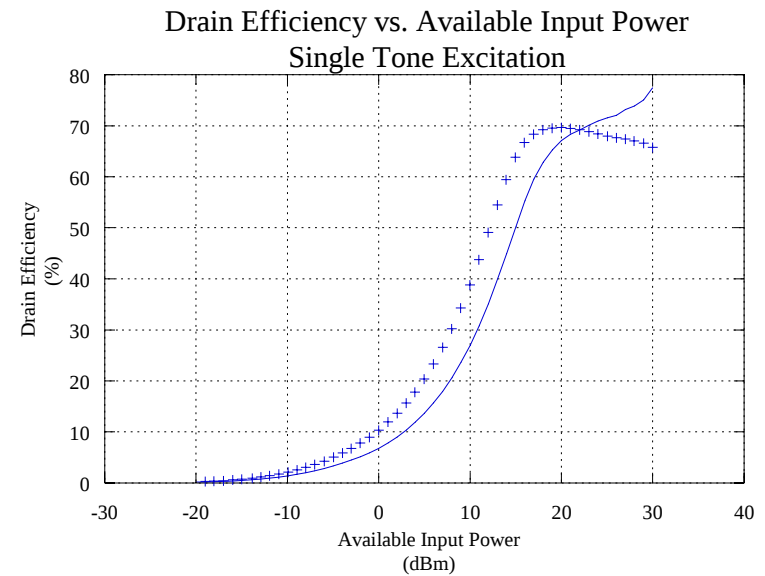
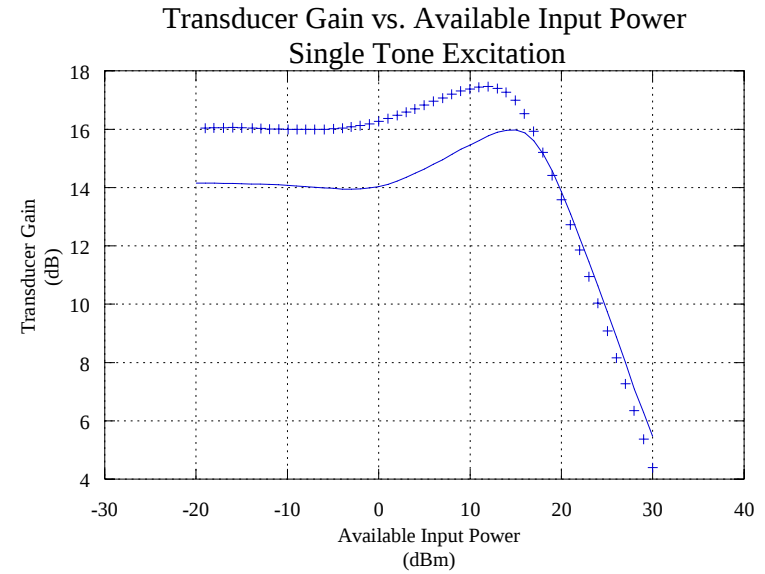
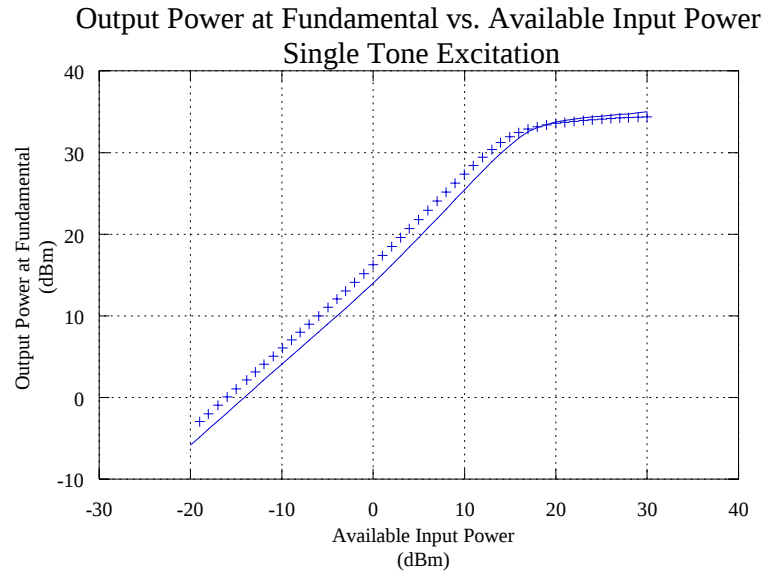
Output Power at 3fo vs. Available Input Power
 Single Tone Excitation



Input Return Loss vs. Available Input Power
 Single Tone Excitation

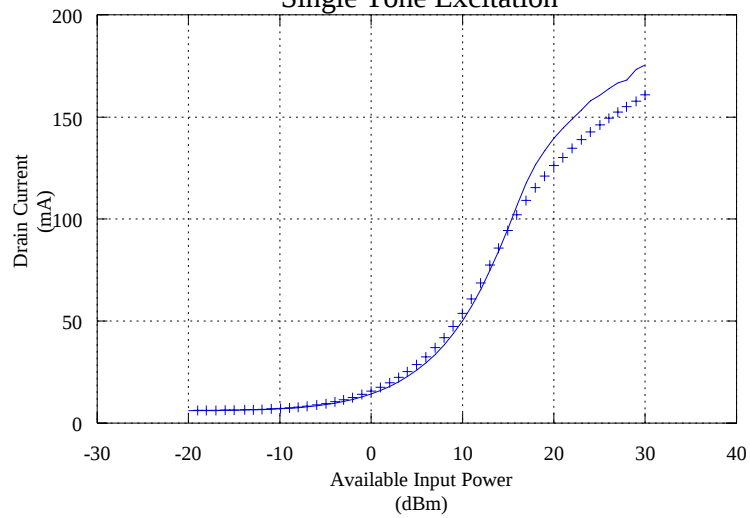


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 Tuned for Efficiency
 Solid: Simulated & Points: Measured

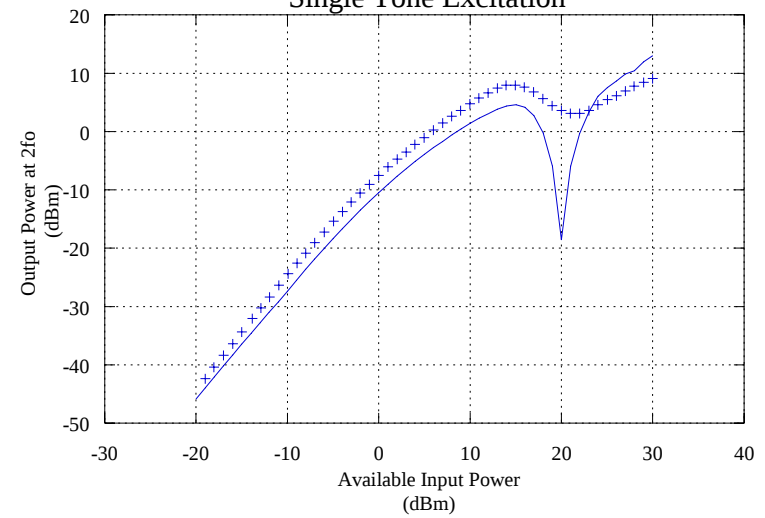


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 Tuned for Efficiency
 Solid: Simulated & Points: Measured

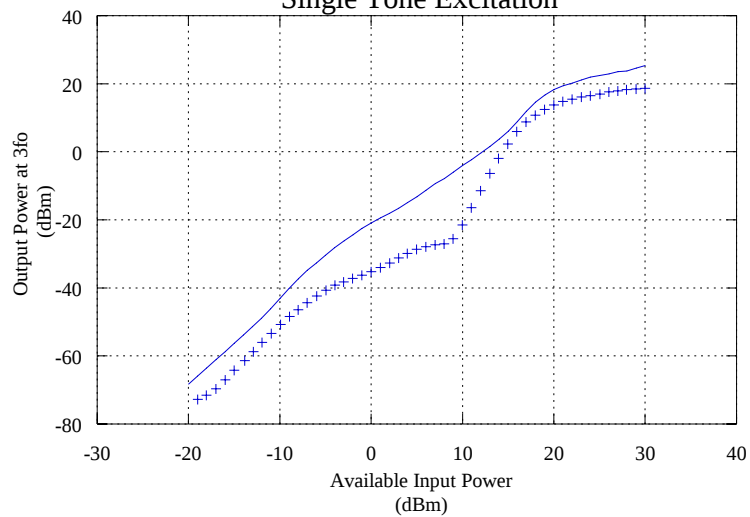
Drain Current vs. Available Input Power
 Single Tone Excitation



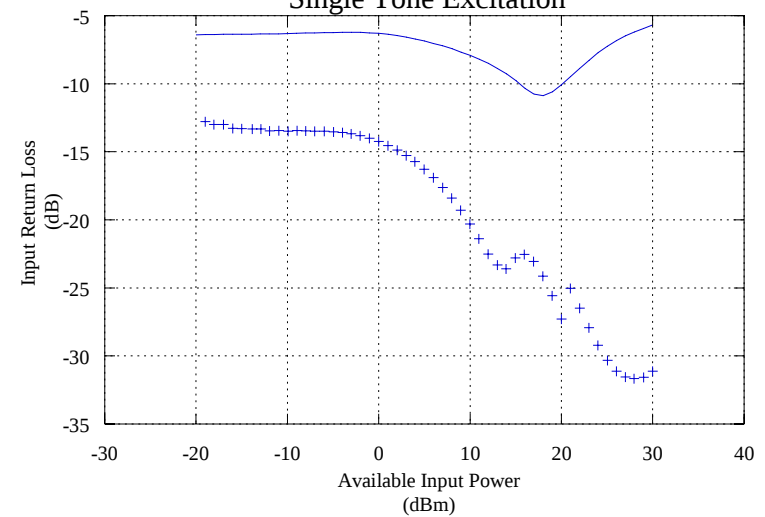
Output Power at 2fo vs. Available Input Power
 Single Tone Excitation



Output Power at 3fo vs. Available Input Power
 Single Tone Excitation

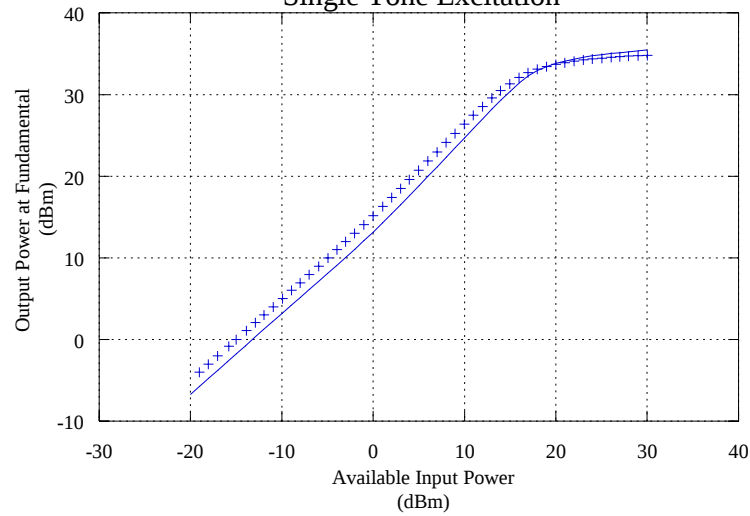


Input Return Loss vs. Available Input Power
 Single Tone Excitation

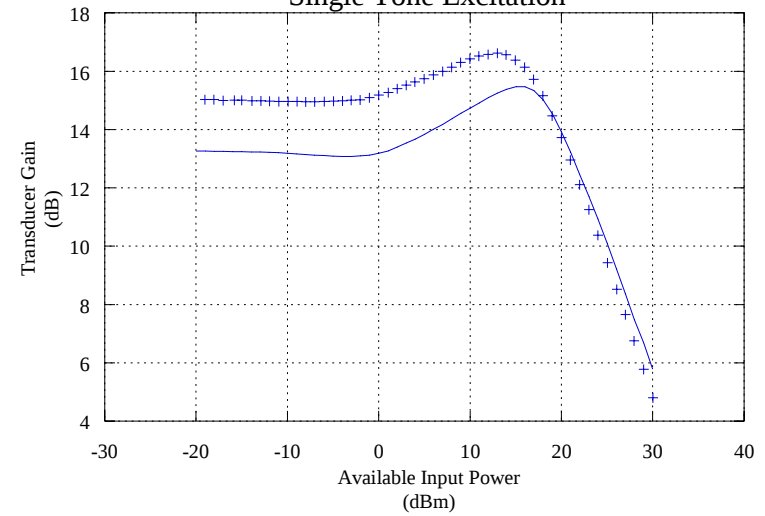


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 Tuned for Power & Efficiency
 Solid: Simulated & Points: Measured

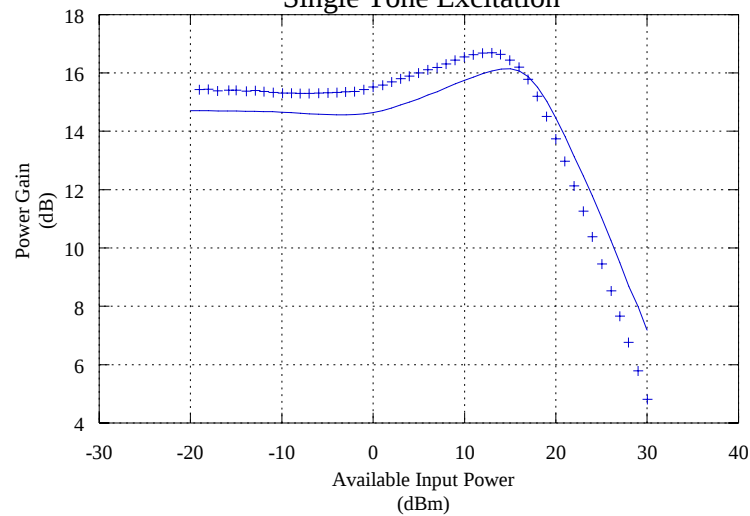
Output Power at Fundamental vs. Available Input Power
 Single Tone Excitation



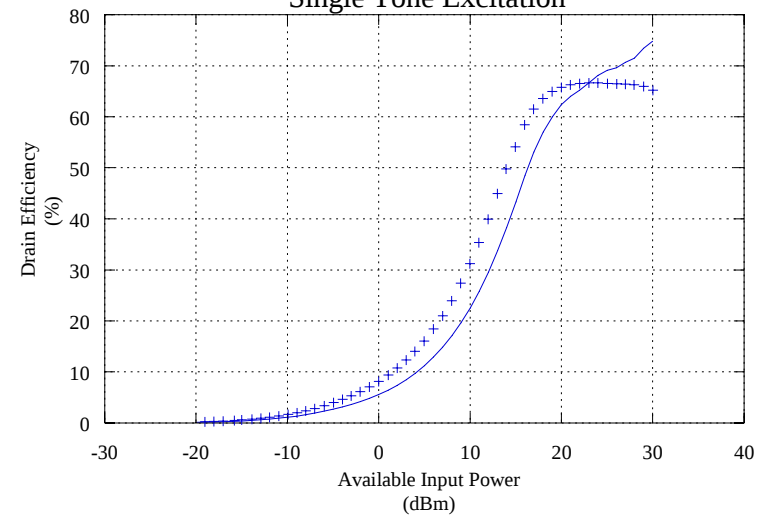
Transducer Gain vs. Available Input Power
 Single Tone Excitation



Power Gain vs. Available Input Power
 Single Tone Excitation

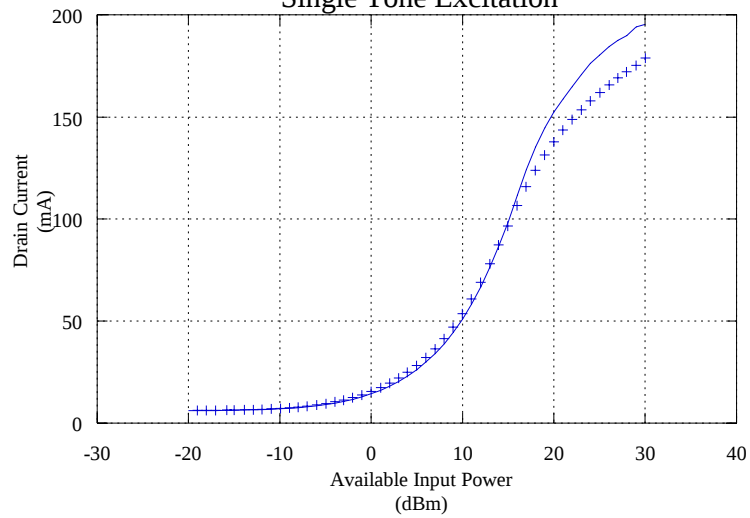


Drain Efficiency vs. Available Input Power
 Single Tone Excitation

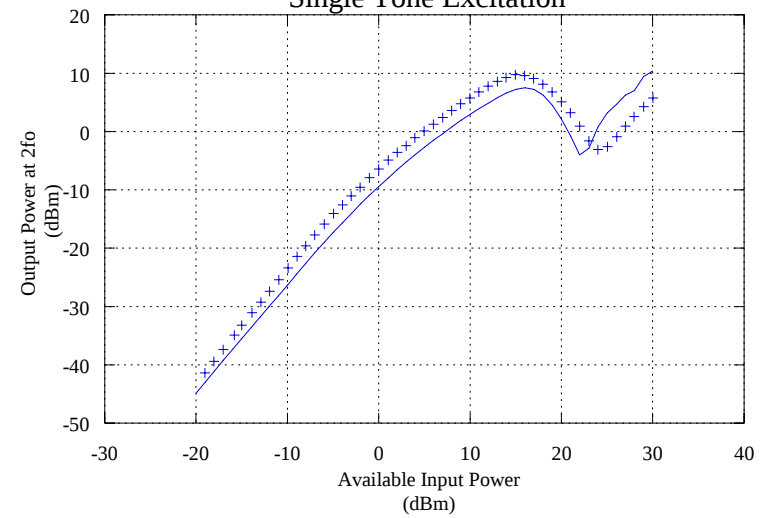


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 Tuned for Power & Efficiency
 Solid: Simulated & Points: Measured

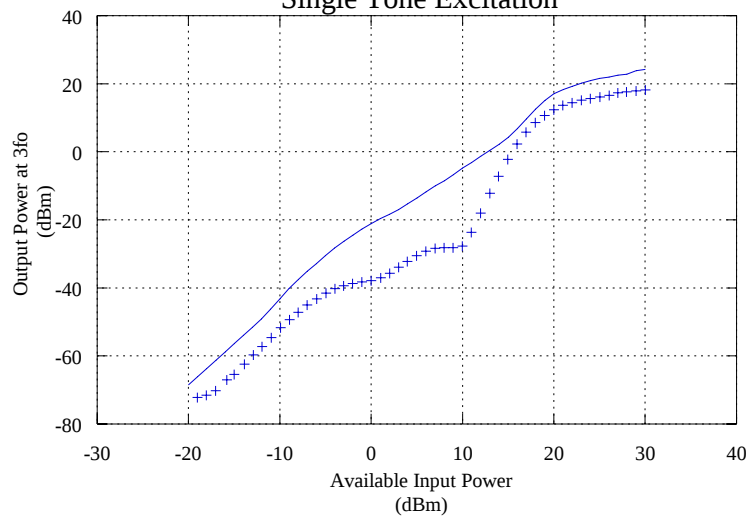
Drain Current vs. Available Input Power
 Single Tone Excitation



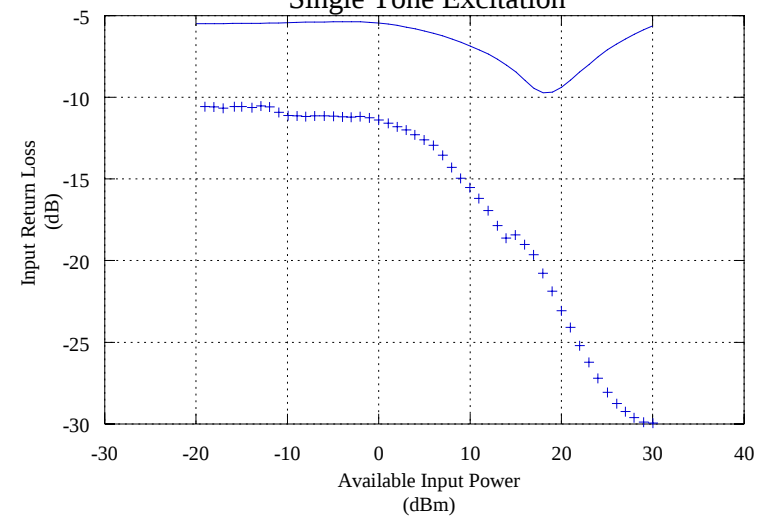
Output Power at 2fo vs. Available Input Power
 Single Tone Excitation



Output Power at 3fo vs. Available Input Power
 Single Tone Excitation



Input Return Loss vs. Available Input Power
 Single Tone Excitation

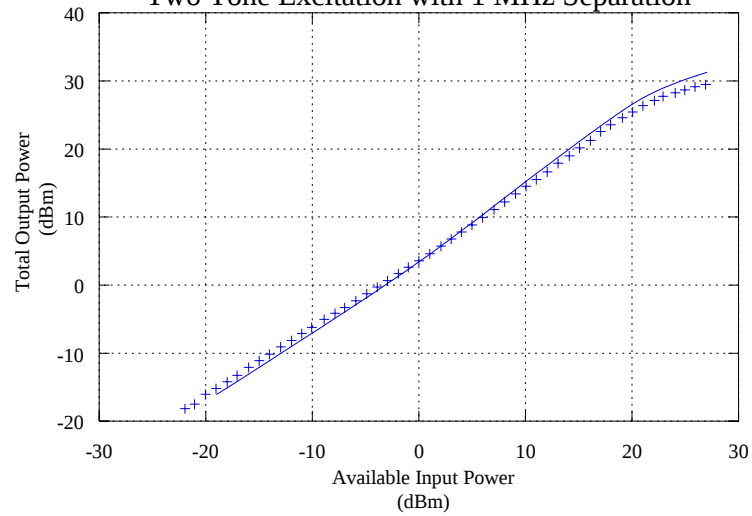




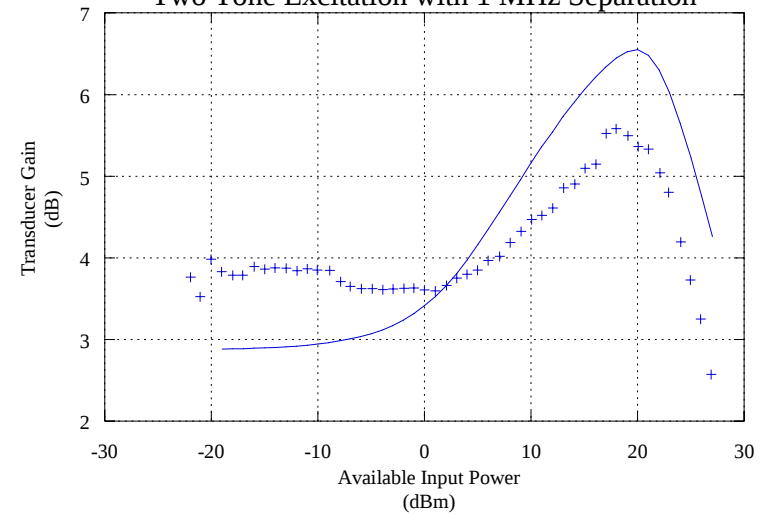
1 Block HV3 LDMOS Device
Number of fingers: 42, Periphery: 2.835 mm
Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
50 ohm Termination
Solid: Simulated & Points: Measured



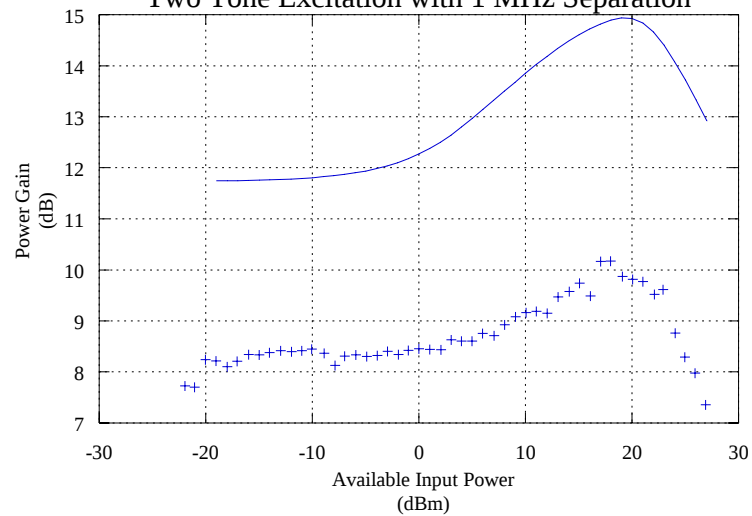
Total Output Power vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



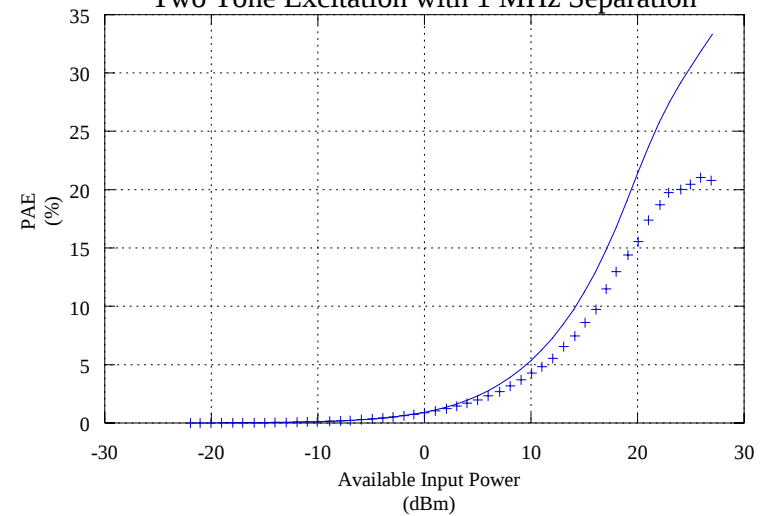
Transducer Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation



Power Gain vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

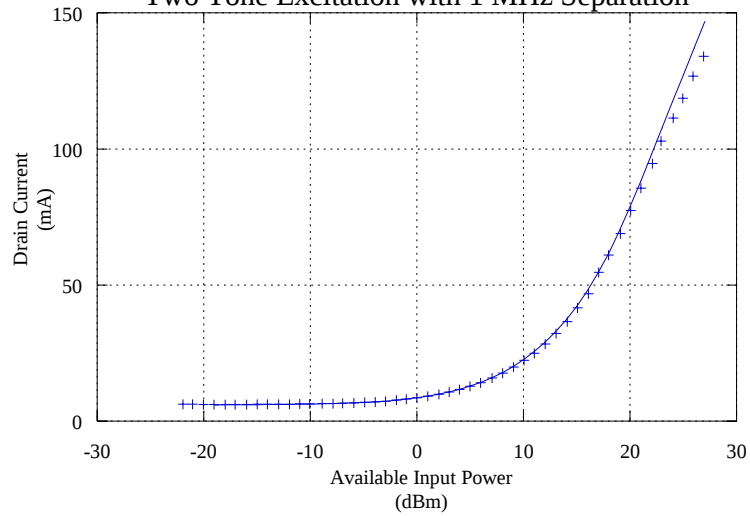


PAE vs. Available Input Power
Two Tone Excitation with 1 MHz Separation

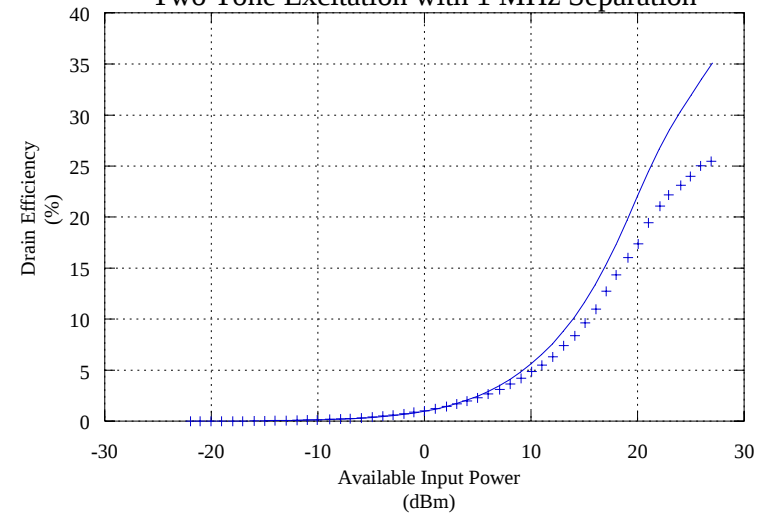


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 50 ohm Termination
 Solid:Simulated & Points:Measured

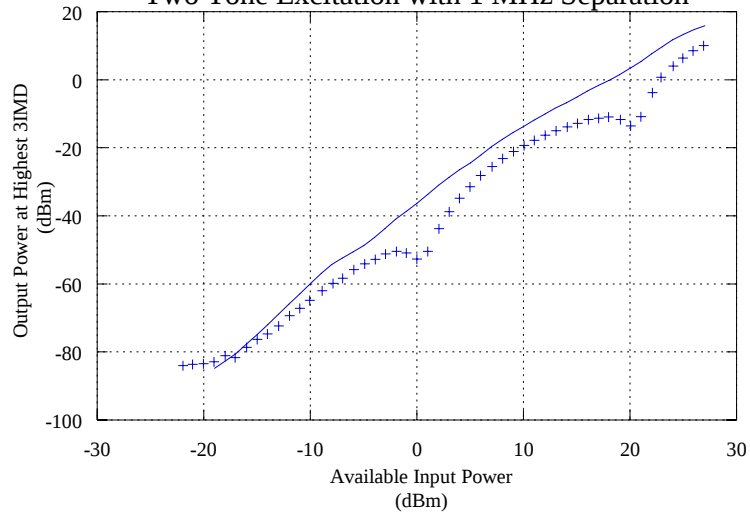
Drain Current vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



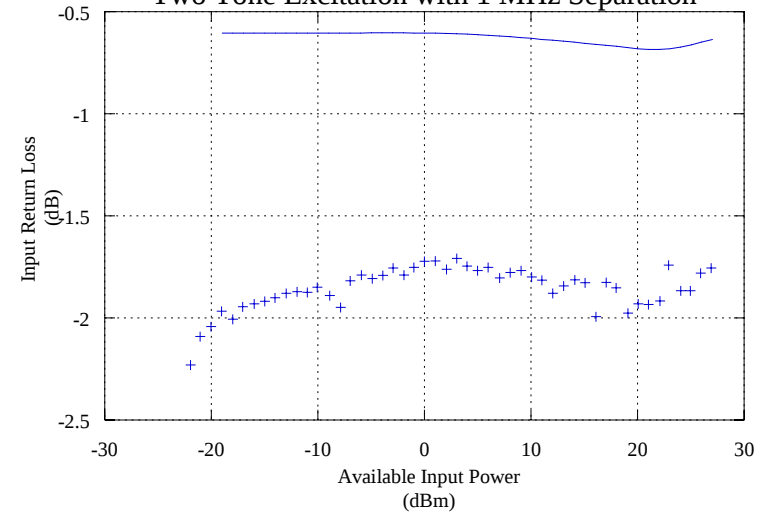
Drain Efficiency vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



Output Power at Highest 3IMD vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



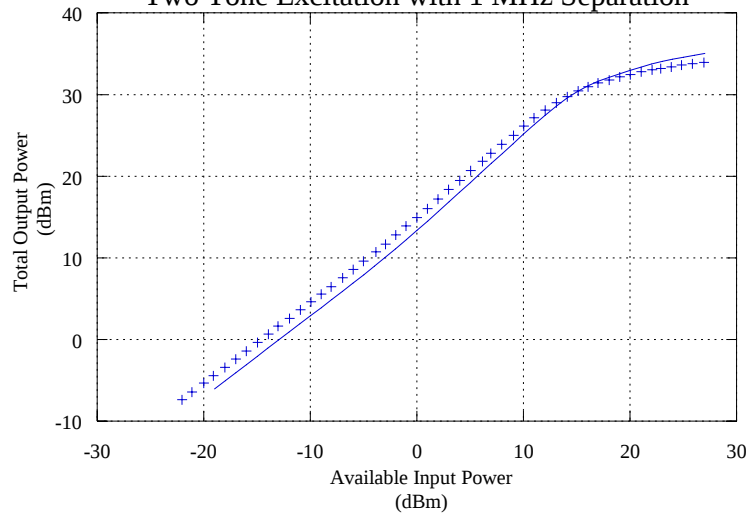
Input Return Loss vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm

Tuned for Power
 Solid: Simulated & Points: Measured

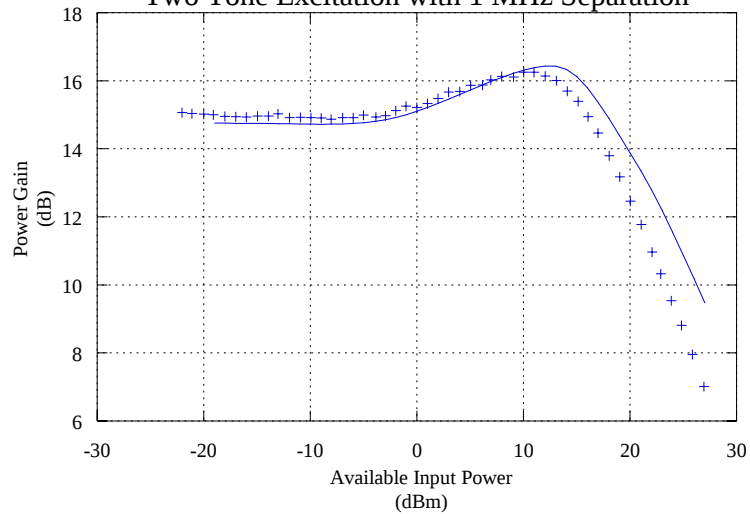
Total Output Power vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



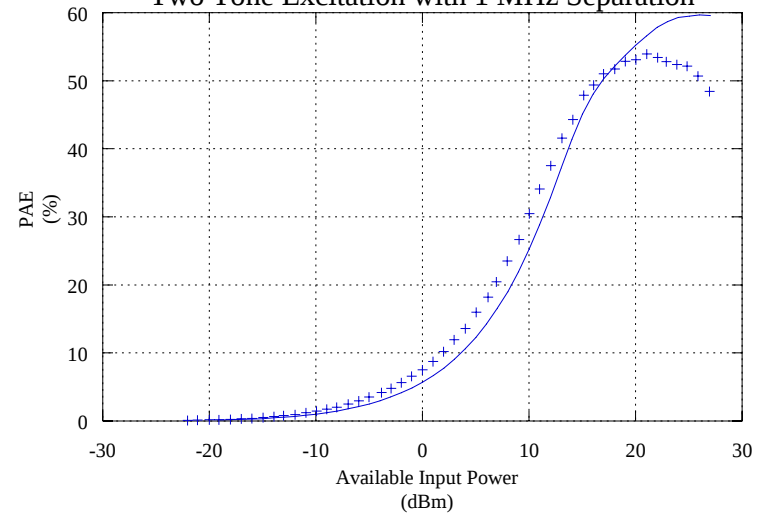
Transducer Gain vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



Power Gain vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation

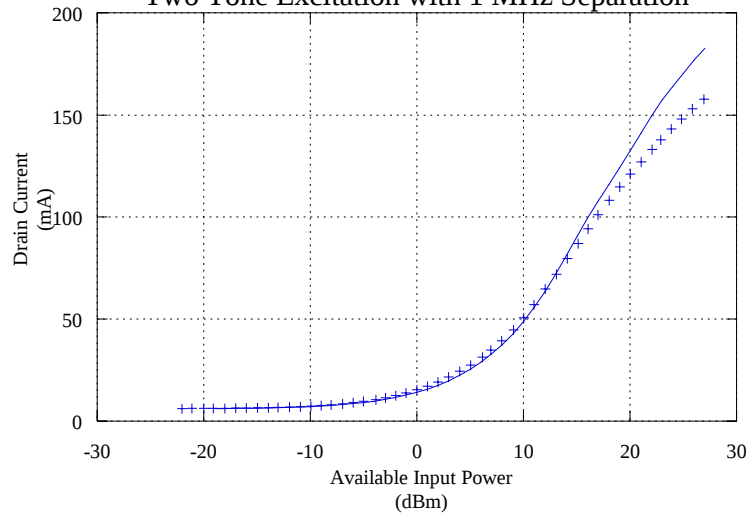


PAE vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation

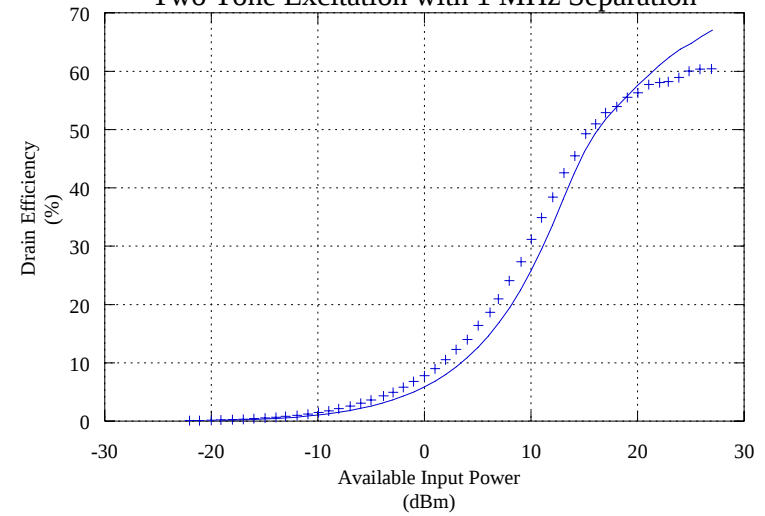


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 Tuned for Power
 Solid: Simulated & Points: Measured

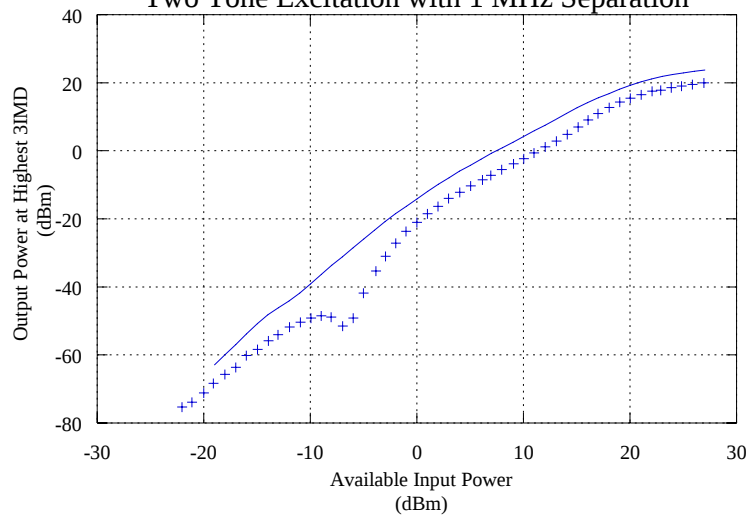
Drain Current vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



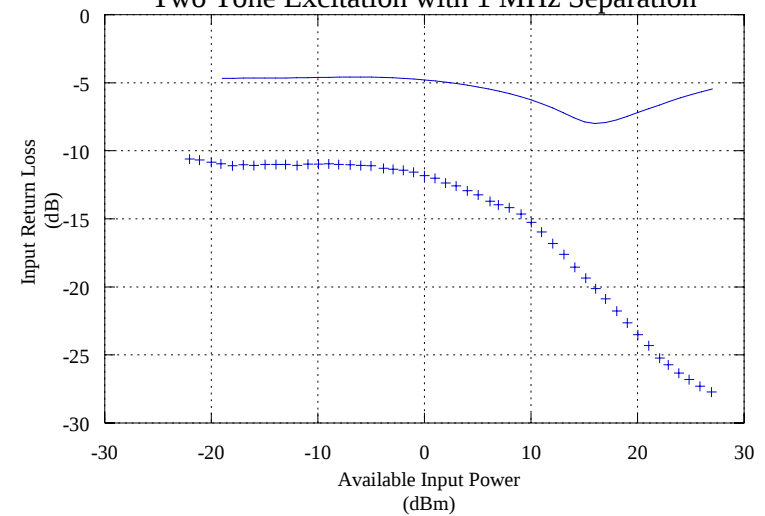
Drain Efficiency vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



Output Power at Highest 3IMD vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation

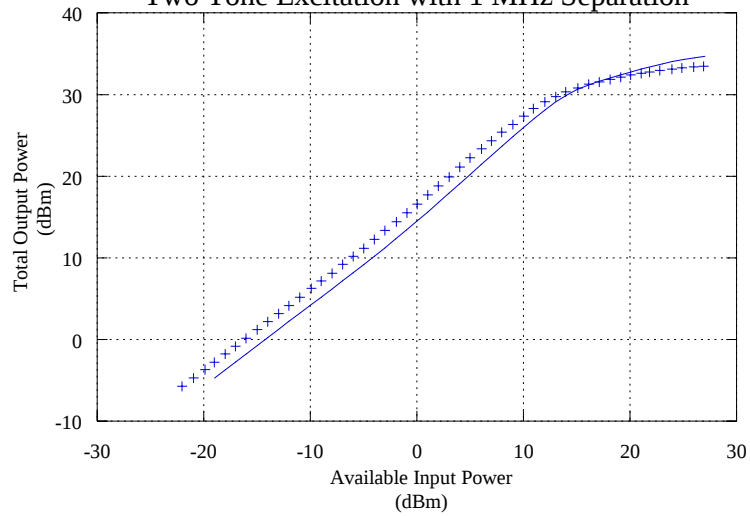


Input Return Loss vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation

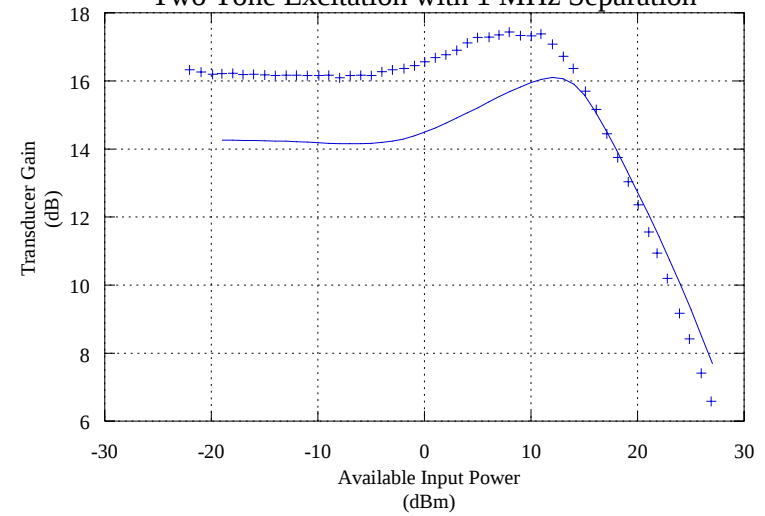


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 Tuned for Efficiency
 Solid: Simulated & Points: Measured

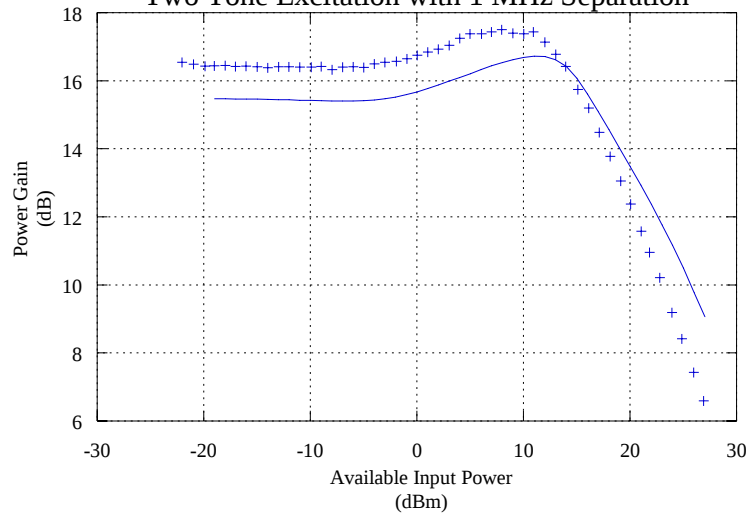
Total Output Power vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



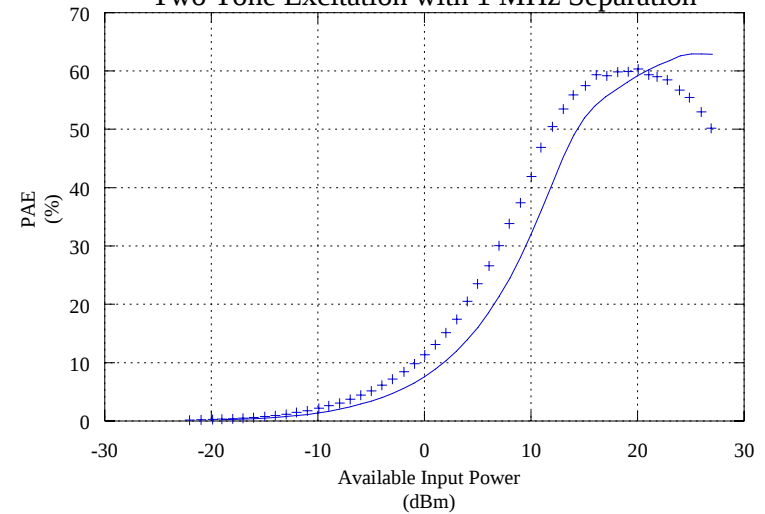
Transducer Gain vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



Power Gain vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation

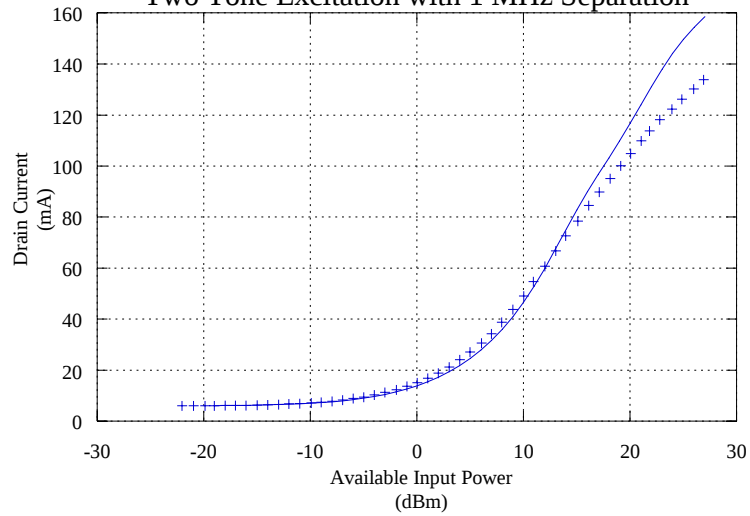


PAE vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation

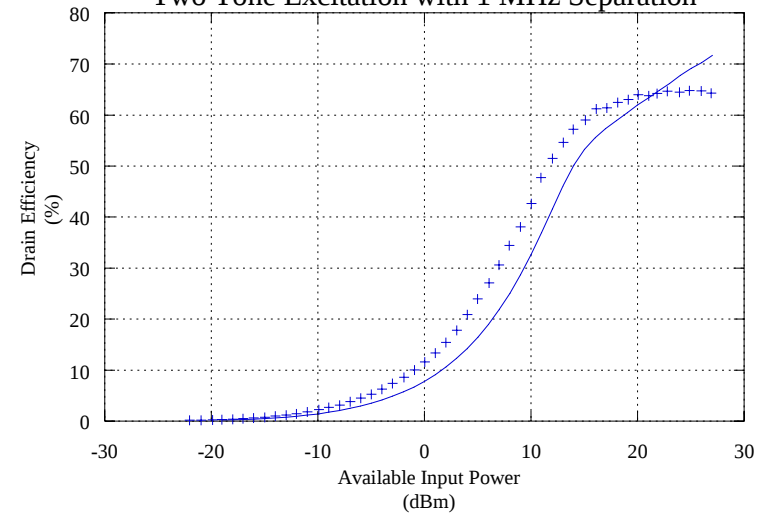


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 Tuned for Efficiency
 Solid: Simulated & Points: Measured

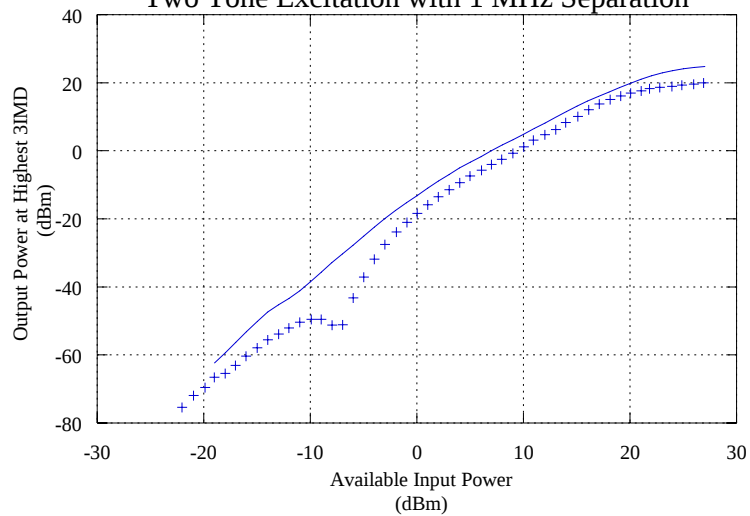
Drain Current vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



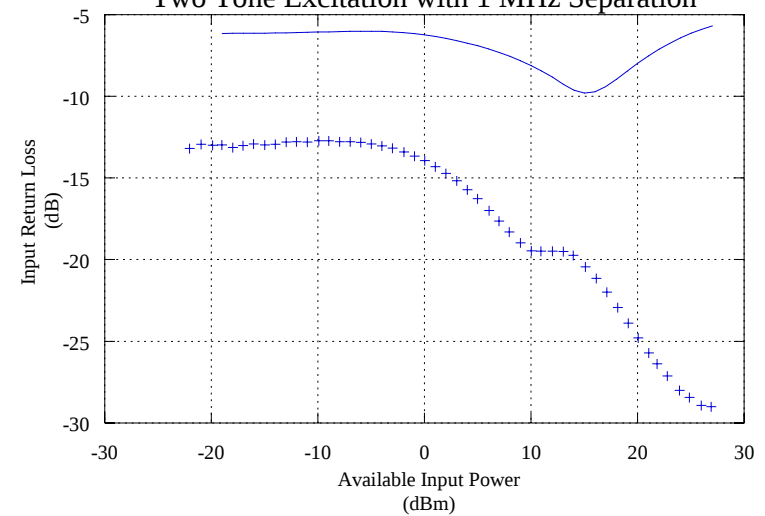
Drain Efficiency vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



Output Power at Highest 3IMD vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation

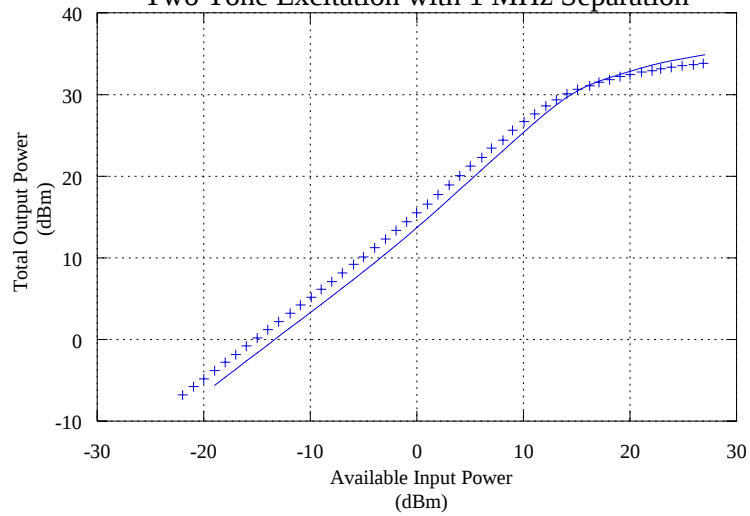


Input Return Loss vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation

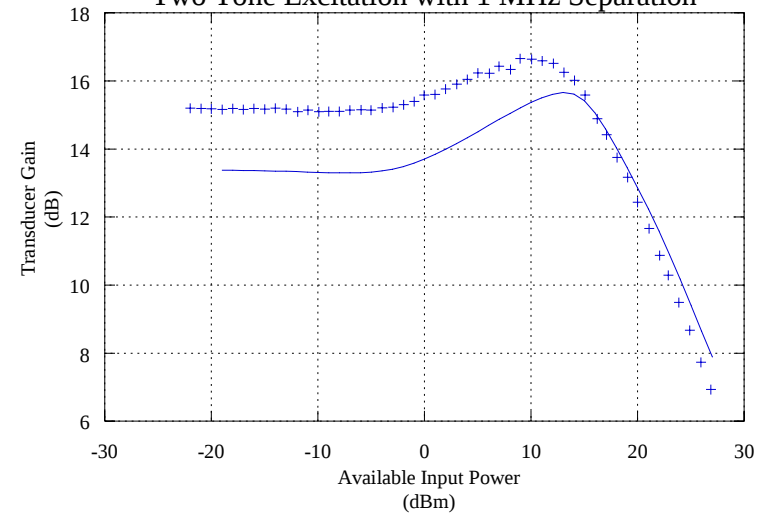


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 Tuned for Power & Efficiency
 Solid: Simulated & Points: Measured

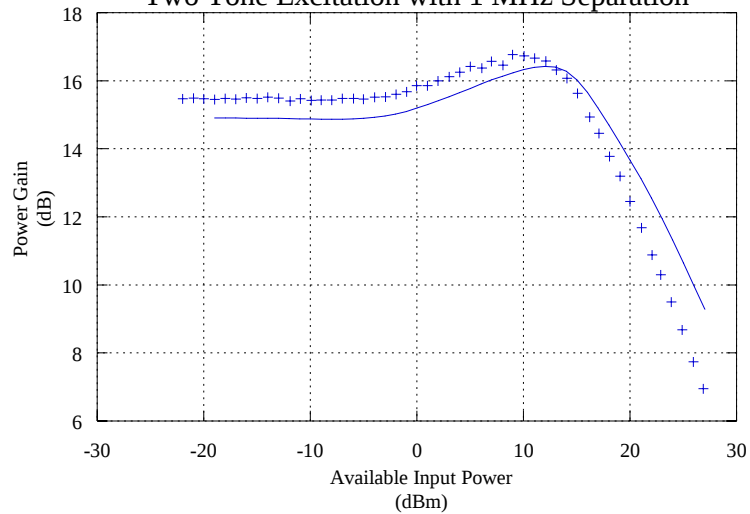
Total Output Power vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



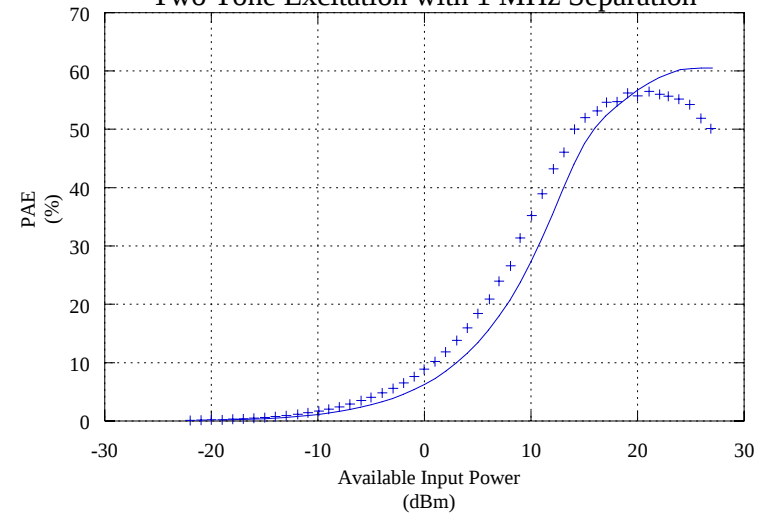
Transducer Gain vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



Power Gain vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation

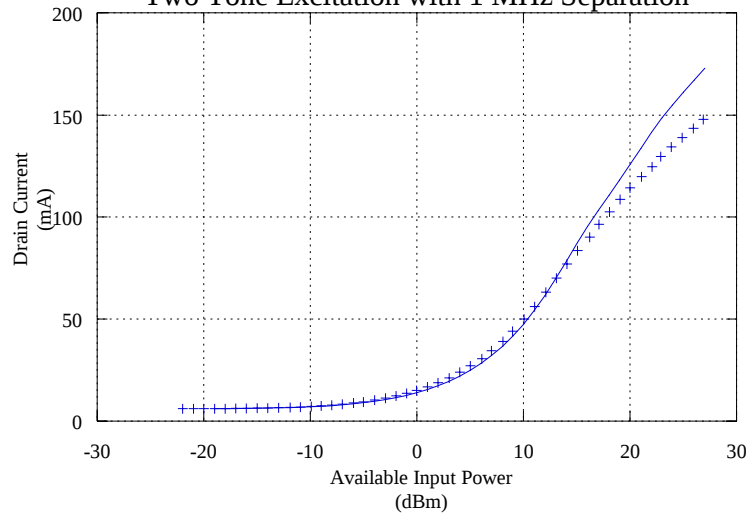


PAE vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation

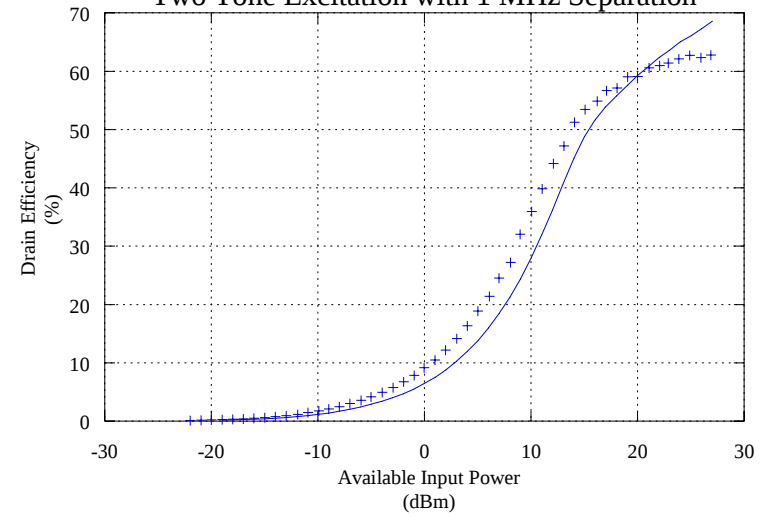


1 Block HV3 LDMOS Device
 Number of fingers: 42, Periphery: 2.835 mm
 Frequency: 2 GHz, $V_{DS}=26$ v & $I_{DS}=2.0$ mA/mm
 Tuned for Power & Efficiency
 Solid: Simulated & Points: Measured

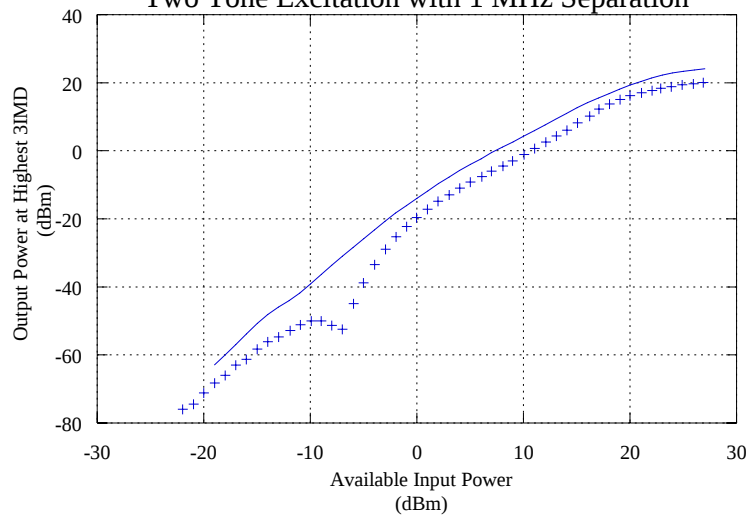
Drain Current vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



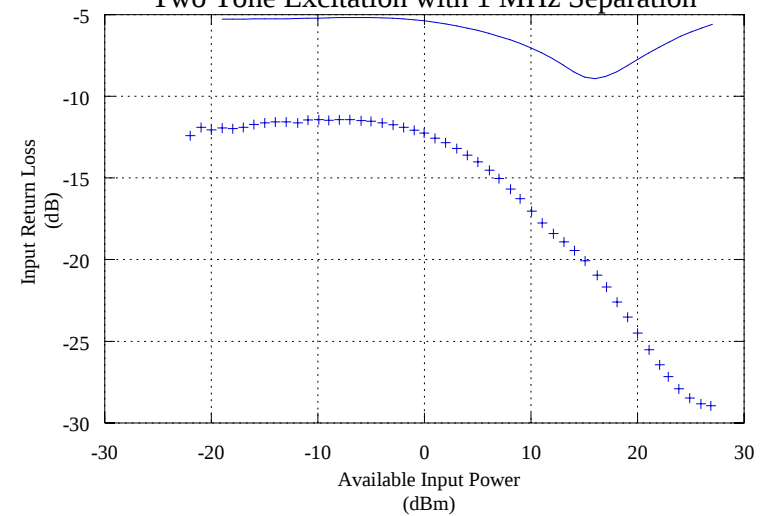
Drain Efficiency vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



Output Power at Highest 3IMD vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



Input Return Loss vs. Available Input Power
 Two Tone Excitation with 1 MHz Separation



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